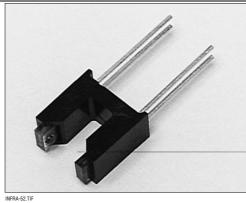
Transmissive Sensor

FEATURES

- Phototransistor output
- Four mounting configurations
- 0.165 in.(4.2 mm) slot width



DESCRIPTION

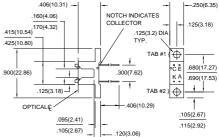
The HOA0825 series consists of an infrared emitting diode facing an NPN silicon phototransistor encased in a black thermoplastic housing. A slot in the housing $% \left(x\right) =\left(x\right) +\left(x\right)$ between emitter and detector provides the means for mechanically interrupting the emitter beam. The phototransistor switching takes place whenever an opaque object passes through the slot between emitter and detector. The HOA0825 series employs plastic molded components. For additional component information see SEP8506 and SDP8406.

Housing material is polycarbonate. Housings are soluble in chlorinated hydrocarbons and ketones. Recommended cleaning agents are methanol and isopropanol.

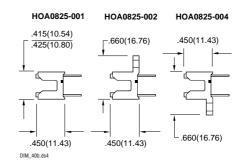
OUTLINE DIMENSIONS in inches (mm)

3 plc decimals ±0.010(0.25) 2 plc decimals ±0.020(0.51)

HOA0825-003



DIM_040.ds4



Honeywell

Honeywell reserves the right to make changes in order to improve design and supply the best products possible.

Transmissive Sensor

ELECTRICAL CHARACTERISTICS (25°C unless otherwise noted)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	TEST CONDITIONS
IR EMITTER						
Forward Voltage	VF			1.6	V	I _F =20 mA
Reverse Leakage Current	I _R			10	μΑ	V _R =3 V
DETECTOR						
Collector-Emitter Breakdown Voltage	V _(BR) ceo	30			V	Ic=100 μA
Emitter-Collector Breakdown Voltage	V _{(BR)ECO}	5.0			V	I _E =100 μA
Collector Dark Current	ICEO			100	nA	V _{CE} =10 V, I _F =0
COUPLED CHARACTERISTICS On-State Collector Current HOA0825-001, -002, -003, -004	Ic(on)	0.5			mA	V _{CE} =0.5 V I _F =20 mA
Collector-Emitter Saturation Voltage	VCE(SAT)			0.4	V	I _F =20 mA Ic=250 μA
Rise And Fall Time	t _r , t _f		15		μs	Vcc=5 V, Ic=1 mA R_L =1000 Ω

ABSOLUTE MAXIMUM RATINGS

(25°C Free-Air Temperature unless otherwise noted)

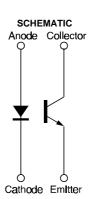
Operating Temperature Range -40°C to 85°C
Storage Temperature Range -40°C to 85°C
Soldering Temperature (5 sec) 240°C

IR EMITTER

Power Dissipation 100 mW (1)
Reverse Voltage 3 V
Continuous Forward Current 50 mA

DETECTOR
Collector-Emitter Voltage 30 V
Emitter-Collector Voltage 5 V

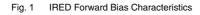
Emitter-Collector Voltage 5 V
Power Dissipation 100 mW ⁽¹⁾
Collector DC Current 30 mA



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Transmissive Sensor



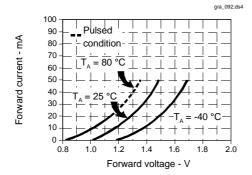
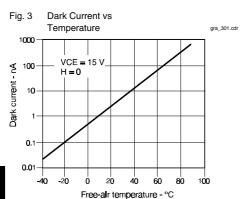
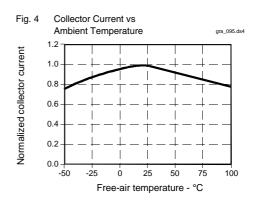


Fig. 2 Non-Saturated Switching Time vs Load Resistance gra_093.dev





All Performance Curves Show Typical Values

Transmissive Sensor

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